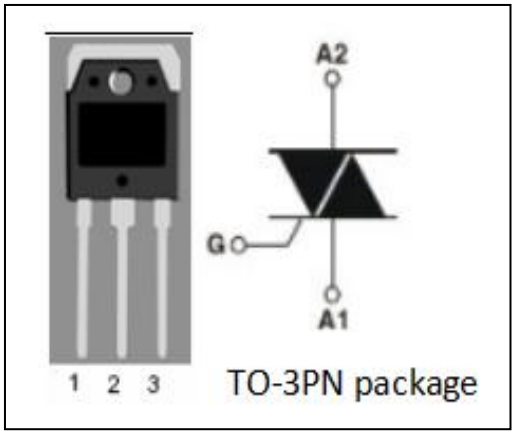
isc Thyristors BTA41-400B

DESCRIPTION

- With TO-3PN packaging
- Can be operated in 4 quadrants
- Advanced technology to provide customers with high commutation performances
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Switching applications
- Phase control
- Static switching on inductive or resistive load

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		MAX	UNIT
V_{DRM}	Repetitive peak off-state voltage		600	V
V_{RRM}	Repetitive peak reverse voltage		600	V
$I_{T(RSM)}$	Average on-state current Tc=75℃		40	A
I_{TSM}	Surge non-repetitive on-state current	50HZ 60HZ	315 300	A
$P_{G(AV)}$	Average gate power dissipation (over any 20 ms period)		1	W
T_j	Operating junction temperature		-40~125	℃
T_{stg}	Storage temperature		-40~150	℃

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ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	V_R=V_{RRM} Rated; V_D=V_{DRM} Rated;	Tj=25℃ Tj=125℃		0.01 6	mA
I_{DRM}	Repetitive peak off-state current					
V_{TM}	On-state voltage	I_T=60A； t_P=380 μ s			1.8	V
I_{GT}	Gate-trigger current	V_D =12V;R_L=33Ω;	Ⅰ		50	mA
			Ⅱ		50	
			Ⅲ		50	
			Ⅳ		100	
V_{GT}	Gate-trigger voltage	V_D =12V;R_L=33Ω;			1.5	V
Rth $_{(j-c)}$	Junction to case				1.2	℃/W